

# isc N-Channel MOSFET Transistor SPD08N50C3, ISPD08N50C3

**• FEATURES**

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 600m\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• DESCRIPTION**

- Improved transconductance

**• ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

| SYMBOL           | PARAMETER                               | VALUE   | UNIT |
|------------------|---|---------|------|
| V <sub>DSS</sub> | Drain-Source Voltage                    | 500     | V    |
| V <sub>GS</sub>  | Gate-Source Voltage                     | ±20     | V    |
| I <sub>D</sub>   | Drain Current-Continuous                | 7.6     | A    |
| I <sub>DM</sub>  | Drain Current-Single Pulsed             | 22.8    | A    |
| P <sub>D</sub>   | Total Dissipation @T <sub>c</sub> =25°C | 83      | W    |
| T <sub>j</sub>   | Max. Operating Junction Temperature     | 150     | °C   |
| T <sub>stg</sub> | Storage Temperature                     | -55~150 | °C   |

**• THERMAL CHARACTERISTICS**

| SYMBOL               | PARAMETER                             | MAX | UNIT |
|----------------------|---------------------------------------|-----|------|
| R <sub>th(j-c)</sub> | Channel-to-case thermal resistance    | 1.5 | °C/W |
| R <sub>th(j-a)</sub> | Channel-to-ambient thermal resistance | 75  | °C/W |



| DIM | mm   |      |
|-----|------|------|
|     | MIN  | MAX  |
| A   | 6.40 | 6.60 |
| B   | 5.20 | 5.40 |
| C   | 1.15 | 1.35 |
| D   | 5.70 | 6.10 |
| F   | 0.65 |      |
| G   | 0.75 |      |
| H   | 2.10 | 2.50 |
| J   | 2.10 | 2.40 |
| K   | 0.40 | 0.60 |
| L   | 0.90 | 1.10 |
| Q   | 9.90 | 10.1 |

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### ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL       | PARAMETER                      | CONDITIONS                      | MIN | TYP | MAX | UNIT      |
|--------------|--------------------------------|---------------------------------|-----|-----|-----|-----------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage | $V_{GS}=0V; I_D=250\ \mu A$     | 500 |     |     | V         |
| $V_{GS(th)}$ | Gate Threshold Voltage         | $V_{DS}=V_{GS}; I_D=350\ \mu A$ | 2.1 |     | 3.9 | V         |
| $R_{DS(on)}$ | Drain-Source On-Resistance     | $V_{GS}=10V; I_D=4.6A$          |     |     | 600 | $m\Omega$ |
| $I_{GSS}$    | Gate-Source Leakage Current    | $V_{GS}=20V$                    |     |     | 0.1 | $\mu A$   |
| $I_{DSS}$    | Drain-Source Leakage Current   | $V_{DS}=500V; V_{GS}=0V$        |     |     | 1   | $\mu A$   |
| $V_{SD}$     | Diode forward voltage          | $I_F=I_S, V_{GS}=0V$            |     |     | 1.2 | V         |